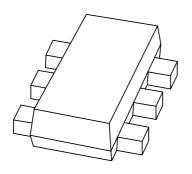
DISCRETE SEMICONDUCTORS

DATA SHEET



PEMX1 NPN general purpose double transistor

Product data sheet Supersedes data of 2001 Aug 30 2001 Nov 07



NPN general purpose double transistor

PEMX1

FEATURES

- 300 mW total power dissipation
- Very small 1.6 mm x 1.2 mm ultra thin package
- · Excellent coplanarity due to straight leads
- Replaces two SC-75/SC-89 packaged transistors on same PCB area
- · Reduced required PCB area
- · Reduced pick and place costs.

APPLICATIONS

· General purpose switching and amplification.

DESCRIPTION

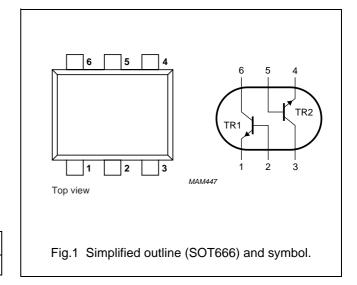
NPN double transistor pair in a SOT666 plastic package. PNP complement: PEMT1.

MARKING

TYPE NUMBER	MARKING CODE
PEMX1	ZZ

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT			
Per transis	Per transistor							
V _{CBO}	collector-base voltage	open emitter	_	50	V			
V_{CEO}	collector-emitter voltage	open base	_	40	V			
V _{EBO}	emitter-base voltage	open collector	-	5	V			
I _C	collector current (DC)		_	100	mA			
I _{CM}	peak collector current		_	200	mA			
I _{BM}	peak base current		-	200	mA			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW			
T _{stg}	storage temperature		-65	+150	°C			
Tj	junction temperature		_	150	°C			
T _{amb}	operating ambient temperature		-65	+150	°C			
Per device	Per device							
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1		300	mW			

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose double transistor

PEMX1

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering is reflow soldering.

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

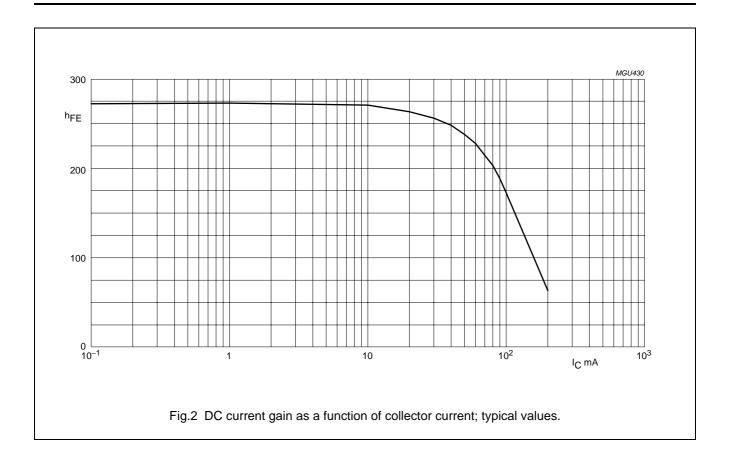
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
Per transis	Per transistor					
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0	_	100	nA	
		$V_{CB} = 30 \text{ V}; I_{E} = 0; T_{j} = 150 ^{\circ}\text{C}$	_	10	μΑ	
I _{EBO}	emitter-base cut-off current	V _{EB} = 4 V; I _C = 0	_	100	nA	
h _{FE}	DC current gain	V _{CE} = 6 V; I _C = 1 mA	120	-		
V _{CEsat}	collector-emitter saturation voltage	$I_C = 50 \text{ mA}$; $I_B = 5 \text{ mA}$; note 1	_	200	mV	
C _c	collector capacitance	$V_{CB} = 12 \text{ V}; I_E = I_e = 0; f = 1MHz$	_	1.5	pF	
f _T	transition frequency	I _C = 2 mA; V _{CE} = 12 V; f = 100 MHz	100	_	MHz	

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN general purpose double transistor

PEMX1



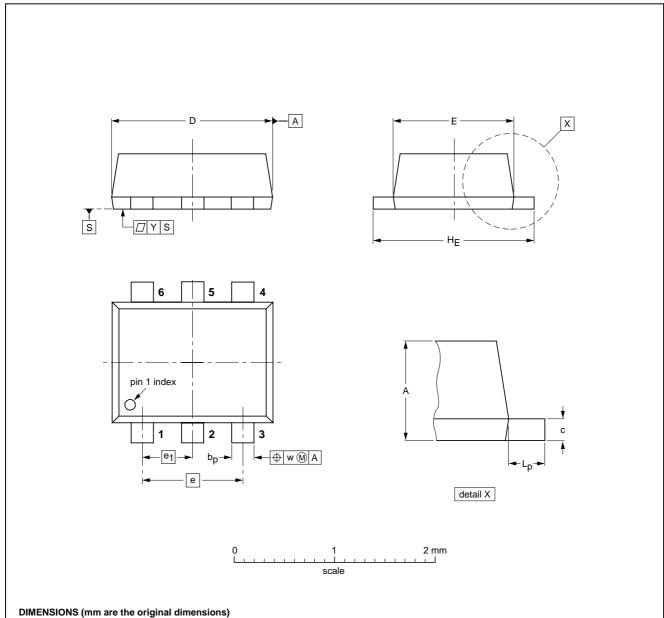
NPN general purpose double transistor

PEMX1

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



DIMENSIONS (mm are the original dimensions))
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UNIT	Α	bp	С	D	E	е	e ₁	HE	L _p	w	у
mm	0.6 0.5	0.27 0.17	0.18 0.08	1.7 1.5	1.3 1.1	1.0	0.5	1.7 1.5	0.3 0.1	0.1	0.1

OUTLINE		REFERENCES				ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						01-01-04 01-08-27

2001 Nov 07 5

NPN general purpose double transistor

PEMX1

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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